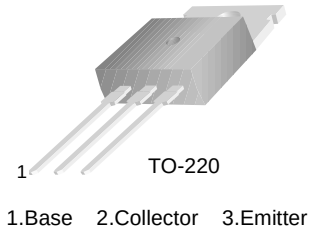


BD240/A/B/C

Medium Power Linear and Switching Applications

- Complement to BD239/A/B/C respectively



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Base Voltage		
	: BD240	- 45	V
	: BD240A	- 60	V
	: BD240B	- 80	V
	: BD240C	- 100	V
V_{CER}	Collector-Emitter Voltage		
	: BD240	- 55	V
	: BD240A	- 70	V
	: BD240B	- 90	V
	: BD240C	- 115	V
V_{EBO}	Emitter-Base Voltage	- 5	V
I_C	Collector Current (DC)	- 2	A
I_{CP}	*Collector Current (Pulse)	- 4	A
I_B	Base Current	- 0.6	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

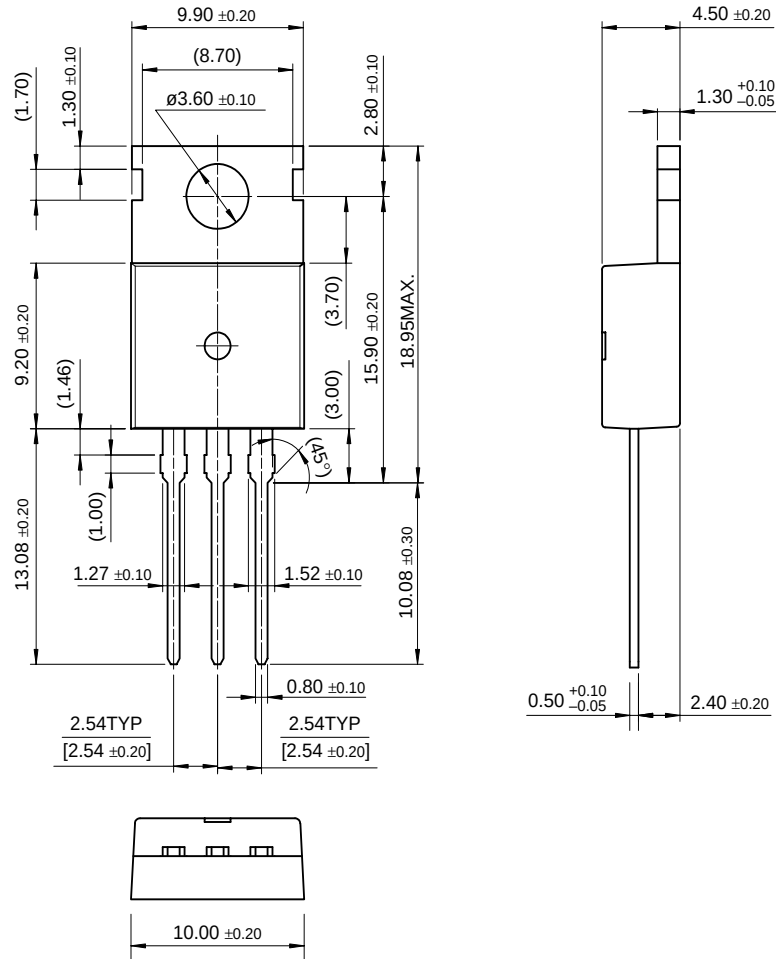
Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage					
	: BD240	$I_C = - 30\text{mA}, I_B = 0$	- 45			V
	: BD240A		- 60			V
	: BD240B		- 80			V
	: BD240C		- 100			V
I_{CEO}	Collector Cut-off Current : BD240/A	$V_{CE} = - 30\text{V}, I_B = 0$			- 0.3	mA
	: BD240B/C	$V_{CE} = - 60\text{V}, I_B = 0$			- 0.3	mA
I_{CES}	Collector Cut-off Current : BD240	$V_{CE} = - 45\text{V}, V_{BE} = 0$			- 0.2	mA
	: BD240A	$V_{CE} = - 60\text{V}, V_{BE} = 0$			- 0.2	mA
	: BD240B	$V_{CE} = - 80\text{V}, V_{BE} = 0$			- 0.2	mA
	: BD240C	$V_{CE} = - 100\text{V}, V_{BE} = 0$			- 0.2	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = - 5\text{V}, I_C = 0$			- 1	mA
h_{FE}	* DC Current Gain	$V_{CE} = - 4\text{V}, I_C = - 0.2\text{A}$	40			
		$V_{CE} = - 4\text{V}, I_C = - 1\text{A}$	15			
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = - 1\text{A}, I_B = - 0.2\text{A}$			- 0.7	V
$V_{BE(on)}$	* Base-Emitter ON Voltage	$V_{CE} = - 4\text{V}, I_C = - 1\text{A}$			- 1.3	V

* Pulse Test: PW=350μs, duty Cycle≤2.0% Pulsed

Package Dimensions

TO-220



Dimensions in Millimeters